

Blue Electrophosphorescent Light-emitting Device Using a Novel Nonconjugated Polymer as Host Materials

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Blue electrophosphorescent organic light-emitting devices (PHOLEDs) were fabricated by doping a phosphorescent iridium complex, bis[(4,6-difluorophenyl)pyridinato-*N,C*']-(picolinate)iridium(III) (Firpic) into a novel nonconjugated polymer, poly[(9,9-diethylfluoren-2,7-ylene)diphenylsilylene] (PF-Si). A device with the same configuration using the widely applied poly(9-vinylcarbazole) (PVK) as the host material was also prepared under the identical conditions for comparison. The luminance and current efficiency of the PF-Si:Firpic device were over four times higher than those of the PVK–Firpic device at a current density of 200 mA/cm² (1260 cd/m² vs 275 cd/m², 0.61 cd/A vs 0.13 cd/A).

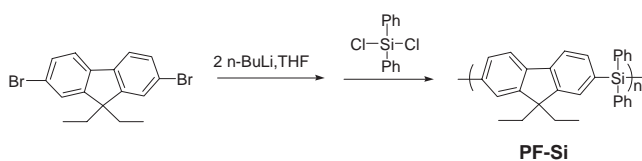
Recently, there have been a number of studies on organic light-emitting devices (OLED) using heavy-metal phosphorescent materials as emitters.^{1–3} Most of the electrophosphorescent devices (so called PHOLED) have a composite guest/host emitter layer, where the guest is a phosphorescent dye with efficient intersystem crossing and the host is a suitably chosen fluorescent organic molecule.^{4,5} Both singlet and triplet excitons formed in the host material can be transferred to the phosphorescent dopant,^{6–8} resulting in very high external quantum efficiency of PHOLEDs.^{9–11} However, as the triplet energy of the phosphor is shifted to blue, it becomes increasingly difficult to find an appropriate host with a suitable high-energy triplet state. Some low molecular weight host materials with high triplet energy, such as *m*-bis(*N*-carbazolyl)benzene (mCP) and bis(triphenylsilane)benzene (UGH2), were applied in blue PHOLEDs to achieve high external quantum efficiency ($\eta_{\text{ext}} = 7.5^{12}$ and 9.1%,¹³ respectively). To our knowledge, polymer-based high energy host materials suitable for blue PHOLEDs have not been well developed, although poly(9-vinylcarbazole) (PVK)-based host–guest systems were reported.^{14–17} The using of nonconjugated polymer host result to PHOLEDs with good external quantum efficiencies, due to the less favorable phosphorescence quenching because of the absence of low-energy triplet state.^{15,16} In this letter, we present a blue phosphorescent device using a novel nonconjugated polymer, poly[(9,9-diethylfluoren-2,7-ylene)diphenylsilylene] (PF-Si)¹⁸ as the host material doped with iridium(III)

bis[(4,6-difluorophenyl)pyridinato-*N,C*']picolinate (Firpic) as an emitter.

The electrophosphorescent polymer light-emitting devices (PHPLEDs) was prepared as follows: A pre-cleaned ITO-coated glass substrate was first coated with a 30 nm-thick layer of poly(ethylenedioxythiophene):poly(styrenesulfonic acid) (PEDOT:PSS) in order to enhance hole injection and improve smoothness of the substrate; Next, a mixture of blue phosphorescent emitter, Firpic, and polymer host, PF-Si, was spin coated from toluene solution, with a doped ratio of 5% (by weight), resulting in a 60 nm-thick emitting layer; After removal of solvent, a 20 nm-thick 2,2',2''-(1,3,5-benzenetriyl)-tris(1-phenyl-1*H*-benzimidazole) (TPBI) hole-blocking layer was applied by thermal vacuum evaporation at a pressure of $<10^{-6}$ Torr; Finally, a 100 nm-thick Al cathode was deposited in vacuum through a shadow mask with 1 mm-diameter circular openings. For comparison, we also fabricated a device with the same configuration using PVK as a host material under the identical conditions. The layer thickness was determined using a crystal thickness monitor, and an ellipsometer for the evaporated and spin-coated films, respectively.

The EL spectra of the devices are shown in Figure 1. A small emission peak (424 nm) was found in the EL spectra of PVK: Firpic device, indicating that the energy transfer from PVK to Firpic was not very completed because that the triplet energy level of Firpic (2.62 eV)¹⁹ is much higher than that of PVK (~ 2.5 eV).²⁰ On the other hand, no emission from PF-Si was observed in the PF-Si:Firpic device, indicating that more efficient energy transfer from PF-Si to Firpic was achieved. The Commission International de L'Eclairage (CIE) coordinates (x and y values, respectively) for PVK and PF-Si devices are (0.15, 0.28) and (0.17, 0.33), respectively.

Figure 2 shows the luminance–voltage (L–V), current–voltage



Scheme 1. Synthetic route of the polymer.

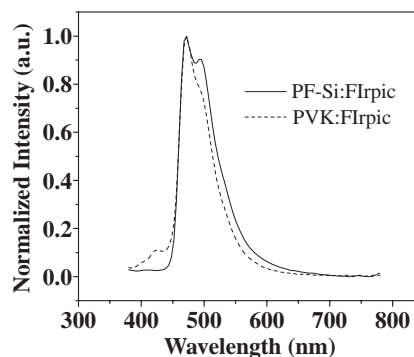


Figure 1. Normalized electroluminescence (EL) spectra of the devices.

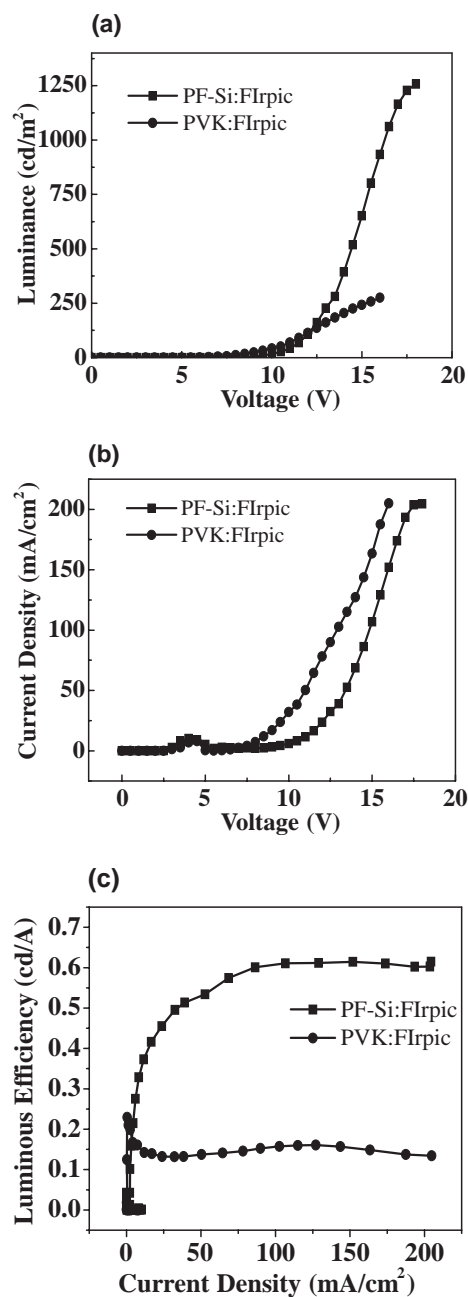


Figure 2. (a) Luminance–voltage, (b) current density–voltage, and (c) luminous efficiency–current density characteristics of ITO/PEDOT:PSS/polymer:Flrpic/TPBI/Al devices.

age (I–V) characteristics, and the luminous efficiency of these devices. The PF-Si:Flrpic device produces a luminance of 1260 cd/m² and a luminous efficiency of 0.61 cd/A at a current density of 200 mA/cm², which were over four times higher than those of the PVK:Flrpic device (275 cd/m² and 0.13 cd/A, respectively).

In conclusion, a blue electrophosphorescent organic light-

emitting device with phosphorescent emitter doped into a novel nonconjugated polymer, PF-Si, was fabricated. Over four times higher luminance and luminous efficiency than those of the PVK:Flrpic device was achieved. It may be attribute to a more efficient energy transfer from the polymer host to the phosphorescent guest in the PF-Si:Flrpic device than in the PVK:Flrpic device. This new polymer could be a potential candidate for the application as host materials in PLEDs, especially for blue PLEDs.

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